

Substitute for form 1449B/PTO		COMPLETION DATE OCT 03 2003		Compleat if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Application Number		10/608,432	
		Filing Date		06/30/2003	
		First Name of Inventor		Robert BELLMAN	
		Group Art Unit		2874	
		Examiner Name		Unassigned	
		Attorney Docket Number		064951-0204	
Sheet	2	of	3		

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²
hnh	A16	ARNOLDBIK et al., "Dynamic Behavior of Hydrogen in Silicon Nitride and Oxynitride Films Made by Low-Pressure Chemical Vapor Deposition", The American Physical Society, Physical Review B, Vol. 48, No. 8, Aug. 15, 1993, pp. 5444-5456		
	A17	BOGATYRJOV et al., "Passive Selective Filter for Flattening the Erbium-Doped Fibre Amplifier Gain Spectrum Based on a Feature of the Silicon Oxynitride Fibre Absorption Spectrum", Electronics Letters, Vol. 31, No. 1, Jan. 5, 1995, pp. 61-62		
	A18	BONA et al., "Wavelength Division Multiplexed Add/Drop Ring Technology in Corporate Backbone Networks", Optical Engineering, Vol. 37, No. 12, Dec. 1998, pp. 3218-3228		
	A19	BOSSEBOEUF and BOUCHIER, "Mechanisms of Reactive Ion-Beam Sputtering of Silicon Nitride in Presence of ¹⁵ N- or D-Labeled Ammonia," J. Electrochem. Society, Vol. 133, No. 4, April 1986, pp. 810-816		
	A20	CAVALLARI et al., "Plasma Processing for Silicon Oxynitride Films", J. Electrochem. Soc., Vol. 134, No. 5, May 1987, pp. 1265-1270		
	A21	DENISSE et al., "Annealing of Plasma Silicon Oxynitride Films", J. Appl. Phys., Vol. 60, No. 7, Oct. 1, 1986, pp 2543-2547		
	A22	GERMAN et al., "Silicon-oxynitride Layers for Optical Waveguide Applications," <u>Electrochemical Society Proceedings</u> , Vol. 99-6		
	A23	HABRAKEN et al., "Hydrogen in low-pressure chemical-vapor-deposited silicon (oxy)nitride films," <u>J. Appl. Phys.</u> , January 15, 1986, Vol. 59, No. 2		
	A24	HABRAKEN et al., "Hydrogen in Low-Pressure Chemical-Vapor-Deposited Silicon (Oxy)Nitride Films", J. Appl. Phys. Vol. 59, No. 2, Jan. 15, 1986, pp. 447-453		
	A25	HE et al., "Hydrogen Behavior in PECVD Nitride by SiH ₄ & ND ₃ During RTA," Mat. Res. Soc. Symp. Proc., Vol. 424, Apr. 8-12, 1996, San Francisco, CA pp. 109-114		
	A26	HUBNER, "Strong Bragg Gratings Induced with 248 nm Light in Buried Silicon Exynitride Waveguides," XP-000987165		
	A27	OHRING, "The Materials Science of Thin Films", 1992, pp. 181-184		
✓	A28	SPEAKMAN et al., "Characterization of PECVD Deposited Silicon Oxynitride Thin Films", Vacuum, Vol. 38, No. 3, 1988, pp. 183-188		

Examiner Signature	Hae Moon Hyun	Date Considered	12-3-04
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Sheet 1 of 3		Attorney Docket Number	064951-0204

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
hnh	A1	4,962,065		BROWN et al.	10-09-1990	
	A2	5,062,680		IMAMURA et al.	11-05-1991	
	A3	5,264,724	A	BROWN et al.	1-23-1993	
	A4	5,343,544	A	BOYD et al.	08-30-1994	
	A5	5,694,513	A	OKANIWA	12-02-1997	
	A6	5,979,188	A	OJHA	11-09-1999	
	A7	5,972,765	A	CLARK et al.	11-26-1999	
	A8	6,077,791	A	DeTAR	06-20-2000	
	A9	6,229,949	B1	IDO et al.	05-08-2001	
	A10	6,341,190	B1	SUMMERSGILL et al.	01-22-2002	
	A11	6,393,185	B1	DEACON	05-21-2002	
	A12	6,499,318	B1	LEMAIRE et al.	12-31-2002	

FOREIGN PATENT DOCUMENTS								
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		Office ³	Number ⁴	Kind Code ⁵ (if known)				
hnh	A13	WO	01/64594	A1	INTERNATIONAL BUSINESS MACHINES CORPORATION	09-07-2001		
hnh	A14	JP	09-078244		CANON INC.	03-25-1997		
hnh	A15	EP	0 673 895	A2	AT&T CORP.	09-27-1995		

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